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**FAX**

**Date:** June 3, 2004 **Pages (including cover):**  
**To:** Examiner Brewster - USPTO **Fax:** 571-272-1854 **Ph:** 571-272-1854  
**From:** Donald R. Studebaker  
**Message:** U.S. Patent Application No. 09/662,004  
Our Reference: 740819-418

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Docket No. 740819-418

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: )  
Kazuichiro ITONAGA et al. ) Group Art Unit: 2823  
Serial No. 09/662,004 ) Examiner: William M. Brewster  
Filed: September 14, 2000 ) Confirmation No. 9057  
For: METHOD OF FORMING INSULATING ) Date: June 3, 2004  
FILM AND METHOD OF  
FABRICATING SEMICONDUCTOR  
DEVICE

**AMENDMENT PURSUANT TO 37 C.F.R. §1.312**

Mail Stop **Issue Fee**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Prior to issuance, please amend the above-identified application identified in caption as follows:

**IN THE CLAIMS:**

1. (Previously Presented) A method of forming an insulating film on a semiconductor layer, comprising the steps of:

(a) loading a substrate including said semiconductor layer on a lower electrode in a processing chamber; and

(b) generating, within the processing chamber, plasma biased toward said substrate by introducing only oxygen into the processing chamber and with the substrate heated to a temperature of up to 300°C, thereafter subjecting said semiconductor layer to the biased plasma,

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